

**Silicon NPN Power Transistors**

**2N6121 2N6122 2N6123**

**DESCRIPTION**

- With TO-220 package
- Complement to PNP type :  
2N6124 ;2N6125 ;2N6126

**APPLICATIONS**

- For use in power amplifier and switching circuit applications

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

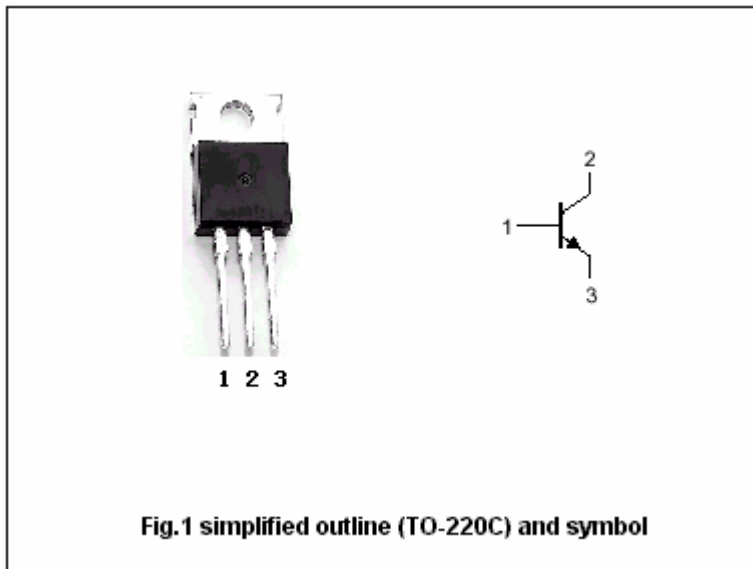


Fig.1 simplified outline (TO-220C) and symbol

**Absolute maximum ratings(Ta=25°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	2N6121	45	V
		2N6122	60	
		2N6123	80	
V <sub>CEO</sub>	Collector-emitter voltage	2N6121	45	V
		2N6122	60	
		2N6123	80	
V <sub>EBO</sub>	Emitter-base voltage	Open collector	5	V
I <sub>C</sub>	Collector current		4	A
I <sub>CM</sub>	Collector current-peak		8	A
I <sub>B</sub>	Base current		1	A
P <sub>T</sub>	Total power dissipation	T <sub>C</sub> =25°C	40	W
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-65~150	°C

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal resistance from junction to case	3.125	°C/W

## Silicon NPN Power Transistors

## 2N6121 2N6122 2N6123

## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT		
V <sub>CE0(SUS)</sub>	Collector-emitter sustaining voltage	2N6121	I <sub>C</sub> =0.1A ; I <sub>B</sub> =0	45			V	
		2N6122		60				
		2N6123		80				
V <sub>CEsat-1</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =1.5A; I <sub>B</sub> =0.15A			0.6	V		
V <sub>CEsat-2</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =4.0A; I <sub>B</sub> =1.0A			1.4	V		
V <sub>BE</sub>	Base-emitter on voltage	I <sub>C</sub> =1.5A ; V <sub>CE</sub> =2V			1.2	V		
I <sub>CEX</sub>	Collector cut-off current	2N6121	V <sub>CE</sub> =45V; V <sub>BE</sub> =1.5V T <sub>C</sub> =125 °C			0.1 2.0	mA	
		2N6122		V <sub>CE</sub> =60V; V <sub>BE</sub> =1.5V T <sub>C</sub> =125 °C				0.1 2.0
		2N6123		V <sub>CE</sub> =80V; V <sub>BE</sub> =1.5V T <sub>C</sub> =125 °C				0.1 2.0
I <sub>CEO</sub>	Collector cut-off current	2N6121	V <sub>CE</sub> =45V; I <sub>B</sub> =0			1.0	mA	
		2N6122		V <sub>CE</sub> =60V; I <sub>B</sub> =0				
		2N6123		V <sub>CE</sub> =80V; I <sub>B</sub> =0				
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			1.0	mA		
h <sub>FE-1</sub>	DC current gain	2N6121	I <sub>C</sub> =1.5A ; V <sub>CE</sub> =2V	25		100		
		2N6122						
		2N6123						20
h <sub>FE-2</sub>	DC current gain	2N6121	I <sub>C</sub> =4A ; V <sub>CE</sub> =2V	10				
		2N6122						
		2N6123						7
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =1A ; V <sub>CE</sub> =4V	2.5			MHz		

